Silicon NPN Power Transistors 2SD1175

DESCRIPTION

- With TO-3 package
- Built-in damper diode
- High voltage ,high power dissipation
- Wide area of safe operation

APPLICATIONS

- Line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
P_T	Total power dissipation	T_C=25℃	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=500mA; I_C=0;	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4.0 A;I_B=0.8 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4.0 A;I_B=0.8 A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=750V;I_E=0			50	μA
		V_{CB}=1500V;I_E=0			1.0	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	10		30	
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=10V	5			
V_F	Diode forward voltage	I_F=4A			2.5	V

PACKAGE OUTLINE

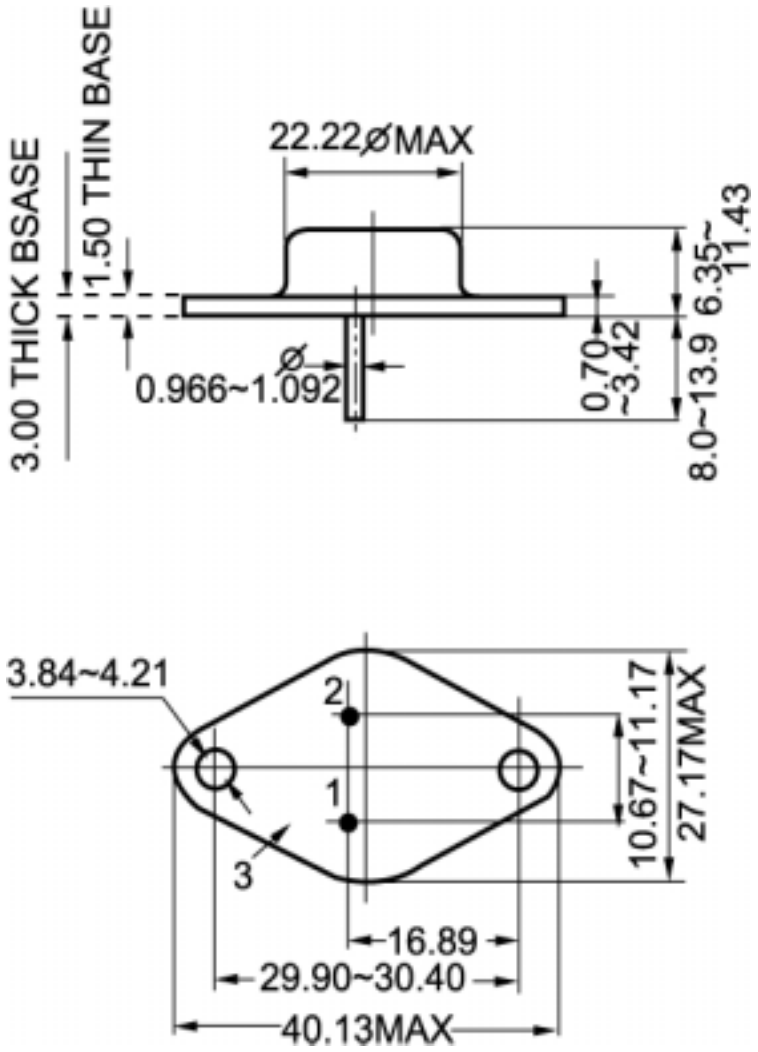

Fig.2 Outline dimensions